Supporting information

Engineering the energy gap near the valence band edge in Mn-incorporated Cu₃Ga₅Te₉ for an enhanced thermoelectric performance Jiaolin Cui,^{a*} Zheng Sun,^{a,b} Zhengliang Du,^a Yimin Chao^{c*}

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Fig.S1 X-ray diffraction patterns of $Cu_{3-x}Ga_5Mn_xTe_9$ powders.

Table S1 Chemical compositions (relative molars) identified for x=0, 0.2 in Cu_{3-x}Ga₅Mn_xTe₉ (taken from a mapping)

Compounds	Cu	Ga	Te	Mn
Cu ₃ Ga ₅ Te ₉	3.02	4.95	9.0	
$Cu_{2.8}Ga_5Mn_{0.2}Te_9$	2.78	4.96	9.0	0.13



Fig.S2 EPMA mapping (a-d) of four elements and line scan (e, f) on the sample $Cu_{2.98}Ga_5Mn_{0.2}Te_9$, an insert in Fig.S2b is the Energy dispersive x-ray spectrum.



Fig. S3 XPS spectra of (a) Cu2p, (b) Ga2p, (c) Te3d, and (d) Mn2p for $Cu_{3-x}Ga_5Mn_xTe_9$.



Fig.S4 Thermal diffusivities as a function of temperature for $Cu_{3-x}Ga_5Mn_xTe_9$, and the inset is the densities as a function of Mn content.



Fig.S5 Experimentally determined bandgap E_g of Cu_{3-x}Ga₅Mn_xTe₉. The upper left insert is the full relation of $(Ahv)^2 = (hv-E_g)$, A is the absorption coefficient, hv is the photon energy.